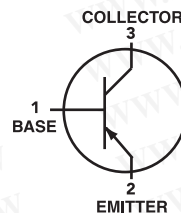


勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
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 Http://www.100y.com.tw

S9012

PNP General Purpose Transistors



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-25	Vdc
Collector-Base Voltage	V_{CBO}	-40	Vdc
Emitter-Base Voltage	V_{EBO}	-5	Vdc
Collector Current-Continuous	I_C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) TA=25°C Derate above 25°C	P_D	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) TA=25°C Derate above 25°C	P_D	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	2.4	mW/°C
Junction and Storage, Temperature	T_J, T_{stg}	417	°C/W
		-55 to +150	°C

DEVICE MARKING

S9012=2T1

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = -0.1\text{mAdc}, I_E = 0$)	$V_{(BR)CEO}$	-25	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -100\mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	-40	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -100\mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ($V_{CE} = -20\text{Vdc}, I_E = 0$)	I_{CEO}	-	-0.1	μAdc
Collector Cutoff Current ($V_{CB} = -40\text{Vdc}, I_E = 0$)	I_{CBO}	-	-0.1	μAdc
Emitter Cutoff Current ($V_{EB} = -5.0\text{Vdc}, I_C = 0$)	I_{EBO}	-	-0.1	μAdc

1.FR-5=1.0 x 0.75 x 0.062 in

2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina

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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C=-50\text{ mAdc}$, $V_{CE}=-1.0\text{ Vdc}$) ($I_C=-500\text{ mAdc}$, $V_{CE}=-1.0\text{ Vdc}$)	$h_{FE}(1)$ $h_{FE}(2)$	120 40	350 -	- -
Collector-Emitter Saturation Voltage ($I_C=-500\text{ mAdc}$, $I_B=-50\text{ mAdc}$)	$V_{CE(sat)}$	-	-0.6	Vdc
Base-Emitter Saturation Voltage ($I_C=-500\text{ mAdc}$, $I_B=-50\text{ mAdc}$)	$V_{BE(sat)}$	-	-1.2	Vdc
Base-Emitter Voltage ($I_E=-100\text{ mA}$)	V_{EBF}	-	-1.4	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C=-20\text{ mAdc}$, $V_{CE}=-6\text{ Vdc}$, $f=30\text{ MHz}$)	f_T	150	-	MHz
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CLASSIFICATION OF h_{FE}

Rank	L	H
Range	120-200	200-350

S9012

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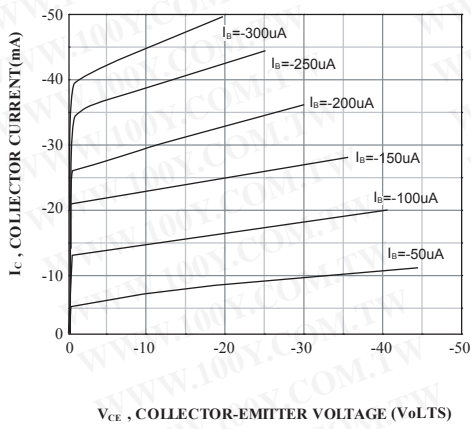


Figure 1. Static Characteristic

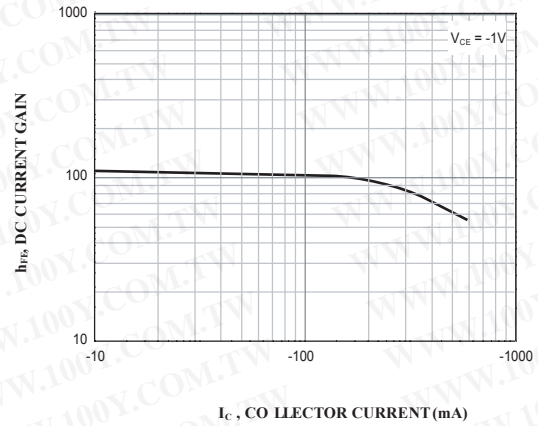


Figure 2. DC current Gain

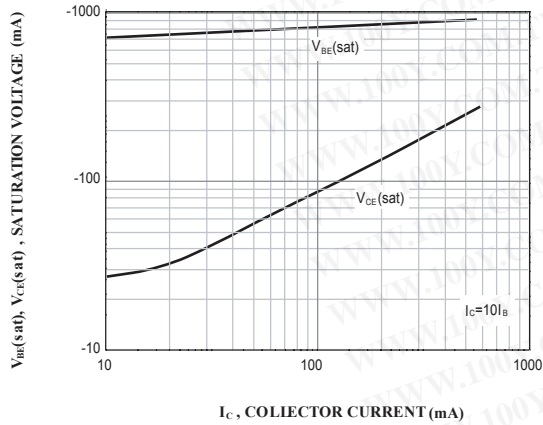


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

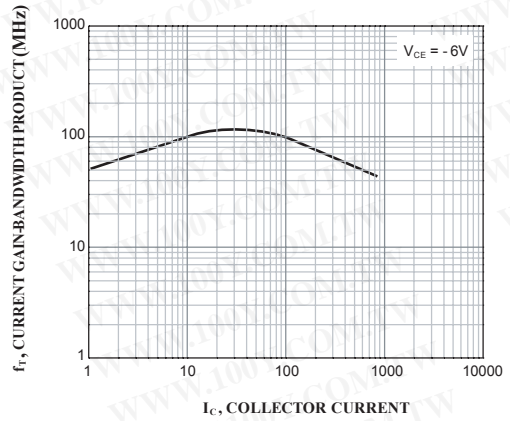


Figure 4. Current Gain Bandwidth Product